## On Electron Transport in $ZrB_{12}$ , $ZrB_2$ and M gB<sub>2</sub>

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W e report on m easurements of the tem perature dependence of resistivity, (T), for single crystal samples of ZrB<sub>12</sub>, ZrB<sub>2</sub> and polycrystalline samples of M gB<sub>2</sub>. It is shown that cluster compound ZrB<sub>12</sub> behaves like a simple metal in the normal state, with a typical B bch – G runeisen (T) dependence. However, the resistive D ebye tem perature,  $T_R = 300$  K, is three times smaller than  $T_D$  obtained from speci c heat data. W e observe the T<sup>2</sup> term in (T) of these borides, which could be interpreted as an indication of strong electron-electron interaction. A lthough the (T) dependence of ZrB<sub>12</sub> reveals a sharp superconductive transition at  $T_c = 6:0$  K, no superconductivity was observed for single crystal samples of ZrB<sub>2</sub> down to 1:3 K.

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It is known that boron has a tendency to form cluster com pounds. In particular there are octahedral B<sub>6</sub> clusters in MeB<sub>6</sub>, icosahedralB<sub>12</sub> clusters in -rhom bohedral boron, and cubo-octahedral  $B_{12}$  clusters in M  $eB_{12}$ . So far, several superconducting cubic hexa - MeB<sub>6</sub> and dodecaborides –  $M \in B_{12}$  have been discovered [1] ( $M \in Sc$ , Y, Zr, La, Lu, Th). M any other cluster borides (M e= Ce, Pr, Nd, Eu, Gd, Tb, Dy, Ho, Er, Tm) were found to be ferrom agnetic or antiferrom agnetic [1, 2]. Even though the superconductivity in  $ZrB_{12}$  was discovered a long time ago ( $T_c = 6 K$ ) [1], there has been little e ort devoted to the study of electron transport and basic superconductive properties of dodecaborides. Only recently, the electron transport of solid solutions  $Zr_1 \times Sc_x B_{12}$  [3] as well as the band structure calculations of  $ZrB_{12}$  [4] has been reported. Understanding the properties of the cluster borides as well as the superconductivity mechanism in these com pounds is very im portant.

Recently, we reported superconductivity at 5:5 K in the polycrystalline samples of  $ZrB_2$  [5]. This was not con med in later studies [6]. It was recently suggested [7] that this observation could be associated with nonstoichiom etry in the zirconium sub-lattice. In this letter we address this problem . We present the results from measurem ent of the tem perature dependencies of resistivity,

(T), for single crystals of  $ZrB_{12}$  and  $ZrB_2$ . C om parative data from polycrystalline samples of M gB<sub>2</sub> are also presented. The superconducting properties of  $ZrB_{12}$  will be published elsewhere.

Under am bient conditions, dodecaboride  $ZrB_{12}$  crystallizes in the fcc structure of the  $UB_{12}$  type (space group Fm 3m), a = 0:7408 nm [8]. In this structure, the Zr atom s are located at interstitial openings in the close-packed  $B_{12}$  clusters [3]. In contrast,  $ZrB_2$  shows a phase consisting of two-dimensional graphite-like m onolayers of boron atom sw ith a honeycom b lattice structure, intercalated with Zrm on olayers (with lattice parameters a = 0.30815 nm and c = 0.35191 nm [5]).

The  $ZrB_2$  powder was produced by the boron carbide reduction of  $ZrO_2$ . The  $ZrB_{12}$  single crystals were obtained from a mixture of a certain amount of  $ZrB_2$  and an excess of boron (50 95%). The resulting materials were subjected to a crucible-free RF-heated zoneinduction melting process in an argon atmosphere. The obtained single crystal ingots of ZrB<sub>12</sub> and ZrB<sub>2</sub> have a typical diam eter of about 5 6 mm and a length of 40 mm. A metallographic investigation detected that the ZrB<sub>2</sub> crystal is surrounded by a polycrystalline rim about 0:5 mm thick. The measured specic density of the  $ZrB_{12}$  rod is 3:60 g=cm<sup>3</sup>, in good agreem ent with the theoretical density. The X-ray di raction m easurem ents con med that both ingots are single crystal. We found the cellparam eters of  $Z_{12}$ , a = 0.74072 0.00005 nm, to be very close to the published values [8].

Polycrystalline M gB<sub>2</sub> and C aM gB<sub>2</sub> sam ples were sintered from m etallic M g or a mixture of C a<sub>i</sub>M g powders and boron pellets using a similar technique as outlined in our earlier work [5]. This technique is based on the reactive liquid M g,C a in Itration of boron. X -ray diraction patterns and optical investigation show large grains of single M gB<sub>2</sub> phase, with much smaller grains of sem iconducting C aB<sub>6</sub> phase visible in-between. D ensity of M gB<sub>2</sub> grains was rather high, 2:4 g=cm<sup>3</sup>, while the sam – ples prepared from M g in Itration had smaller density of 2:2 g=cm<sup>3</sup>. O nly M gB<sub>2</sub> sam ples cut from large grains were studied. These sam ples willbe denoted as C aM gB<sub>2</sub>.

W e used a spark erosion m ethod to cut the sam ples into a parallelepiped with dimensions of about 0.5  $0.5 \ 8 \text{ mm}^3$ . Single crystal sam ples were oriented along <100> for ZrB<sub>12</sub>, and in hexagonal [0001] and basal [1100] directions for ZrB<sub>2</sub>, respectively. The orientation process was perform ed using an X-ray Laue cam era. The

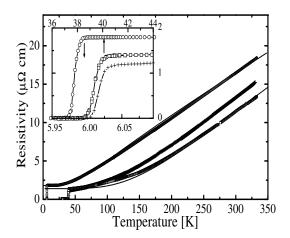


FIG. 1: Tem perature dependence of the resistivity, (T), of  $ZrB_{12}$  single crystal (open circles),  $M \ gB_2$  (squares) and  $C \ aM \ gB_2$  (triangles) samples. The solid lines represent BG ts to the experimental data by Eq.1.

sam ples were lapped by diam ond paste and subsequently etched:  $2rB_{12}$  in hot nitrogen acid,  $2rB_2$  in mixture of  $H_2O_2$ =HNO<sub>3</sub>/HF, and MgB<sub>2</sub> in 2% HClplus water-free ethanol.

A standard four-probe ac (9H z) m ethod was used for resistance m easurem ents. We used Epotek H20E silver epoxy for electrical contacts. The sam ples were m ounted in a a tem perature variable liquid helium cryostat. Tem – perature was measured with platinum (PT-103) and carbon glass (CGR-1-500) sensors. The critical tem perature m easured by RF susceptibility [5] and (T) was found to be  $T_{c0} = 5.97$  K for ZrB<sub>12</sub> sam ples and 39 K for MgB<sub>2</sub> polycrystalline sam ples, respectively.

We display the temperature dependence of the resistivity for  $ZrB_{12}$ , M gB<sub>2</sub> and C aM gB<sub>2</sub> in Fig. 1 and that of  $ZrB_2$  in Fig. 2. To emphasize the variation of (T) in a superconductive state, we plot these data in the inset of Fig. 1. The sam ples demonstrate a rem arkably narrow superconducting transition with T = 0.04 K for ZrB<sub>12</sub> and with T = 0.7 K for both M gB<sub>2</sub> sam ples. Such a transition is a characteristic of good quality sam ples.

As we can see from Fig. 2, no superconductivity was observed in  $ZrB_2$  down to 1:3 K, while a pronounced slope change in (T) is observed around 7 K. One can explain such behavior in the following way. In  $ZrB_2$  the Ferm i level is located in the pseudo gap. The presence of Zr defects in  $Zr_{0:75}B_2$  leads to the appearance of a very intense peak in the density of states in the vicinity of the pseudo gap and subsequent superconductivity [7]. We strongly believe that the observation of [5] was due to nonstoichiom etry of our sam ples. Superconductivity in nonstoicheom etric sam ples is very common in other borides: M  $oB_{2:5}$ , M  $oB_{2:5}$ , M  $o_2B$ , W  $_2B$ , B  $eB_{2:75}$  [9, 10].

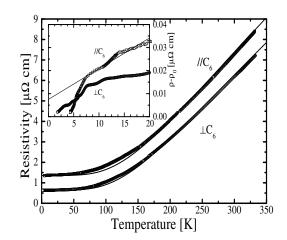


FIG. 2: Temperature dependence of (T) of  $Z_1B_2$  single crystal samples in basal plane (circles) and in c direction (squares).

It is worth noting that  $Z_{1}B_{12}$  is mostly boron, and one could speculate that its resistivity should be rather high. In contrast we observe that the room temperature resistivity of  $Z_{1}B_{12}$  is almost the same as for M gB<sub>2</sub> and  $Z_{1}B_{2}$  samples. The (T) is linear above 90 K with the slope of (T) more pronounced than in M gB<sub>2</sub> or  $Z_{1}B_{2}$ . The residual resistivity ratio RRR of 9.3 for  $Z_{1}B_{12}$  as well as RRR 10 for M gB<sub>2</sub> and  $Z_{1}B_{2}$  sam ples suggests that the samples are in the clean limit. One can predict a nearly isotropic resistivity for fcc  $Z_{1}B_{12}$ , which can be described by the B loch-G runeisen (BG) expression of the electron-phonon e-p scattering rate [11]:

(t) (0) = 4 
$$_{1}t^{5} \int_{0}^{Z_{1=t}} \frac{x^{5}e^{x}dx}{(e^{x} \ 1)^{2}} = 4 _{1}t^{5}J_{5}$$
 (1=t) (1)

Here, (0) is the residual resistivity,  $_1 = d$  (T)=dT is a slope of (T) at high T (T >  $T_R$ ), t = T= $T_R$ ,  $T_R$  is the resistive D ebye tem perature and J<sub>5</sub> (1=t) is the D ebye integral. A swe can see from Fig. 1, all data for ZrB<sub>12</sub> fall very close to the theoretical BG function (solid line). To emphasize the variation of (T) at low T we plot these (0) versus  $t^5 J_5$  (1=t) in Fig. 3 on a log-log data as (T) scale. The BG formula predicts a linear dependence of (0)] versus  $\log [t^5 J_5 (1=t)]$  with the slope equal log[(T)]to unity. We use  $T_{\text{R}}$  as a tting parameter to achieve agreem ent at the high tem peratures. For com parison, we also present our (T) data of  $ZrB_2$  and M gB<sub>2</sub> calculated in a clean case of the two band model [12].

It is clear from Fig. 3 that above 25 K the BG model describes the (T) dependence of  $ZrB_{12}$  fairly well. It is remarkable that this description works wellw ith constant  $T_R = 300$  K. At the same time,  $T_D$  calculated from speci c heat data [13] is three times higher. Furtherm ore

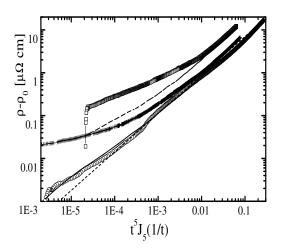


FIG.3: The (T) (0) vs. reduced D ebye integral  $t^5 J_5$  (1=t) for  $ZrB_{12}$  (open circles),  $ZrB_2$  in basal plane (crosses) and C aM gB<sub>2</sub> (squares). The dashed line is (T) of M gB<sub>2</sub> calculated in the two band m odel [12].

 $T_{\rm D}$  increases from 800 K to 1200 K as tem perature varies from  $T_{\rm c}$  up to room temperature. In order to shed light on this discrepancy, we used a model applied to LaB $_6$  of R ef. [14]. We can treat the boron sub-lattice as a D ebye solid with  $T_{\rm R}$  and the Zr ions as independent E instein oscillators with characteristic temperature  $T_{\rm E}$ . The e ect of the E instein mode on the resistivity of a metallic solid is discussed in Ref.[15]:

$$_{\rm E}$$
 (T) =  $\frac{{\rm K} {\rm N}}{{\rm M} {\rm T} (e^{{\rm E} - {\rm T}} {\rm 1})^2}$ : (2)

Here N is the number of oscillators per unit volume, K is a constant that depends on the electron density of the metal, M is the atom ic mass. We t the data by summing Eq. (1) and Eq. (2), and living K N = M, 1, T\_R as free parameters. A lthough them odel calculations perfectly match the data (see solid line in Fig. 3), the T\_E we are getting is unreasonably small (T\_E = 50 K), and the di erence between T\_R and speci c heat T\_D becomes even worse, T\_R = 270 K. We believe that this in-consistency of T\_R and T\_D can be explained by limitation of T\_R by a cut-o phonon wave vector q =  $k_B T = \sim s$ . The latter is limited by the Ferm i surface (FS) diameter  $2k_F$  [16] rather than the highest phonon frequency in the phonon spectrum .

A coording to band structure calculations [4], the FS of ZrB<sub>12</sub> consists of an open sheet along L direction at point with k  $_{\rm X}$  = 0:47 A  $^1$ , a quasi spherical sheet at point X (k<sub>X</sub> = 0:37 A  $^1$ ) and a small sheet at point K (k<sub>K</sub> = 0:14 A  $^1$ ). We suggest that T<sub>R</sub> is limited by the small FS sheet. Unfortunately the experimentalFS m odel and the sound velocity are not yet known.

Therefore we can not corroborate this suggestion by experimentalFS.

A swe can see from Fig.3, the (T) of  $2 rB_2$  and M gB<sub>2</sub> samples deviates from the BG m odel even m ore dram atically. Putti et al. [17] m odi ed the BG equation introducing variable powern for the t<sup>n</sup> J<sub>n</sub> (1=t) term in Eq. (1). The best t to the data was obtained with n = 3 which in fact ignores a sm all angle e-p scattering. Recently Sologubenko et al. [18] reported a cubic T dependence in the a,b plane resistivity below 130 K in the single crystals of M gB<sub>2</sub>. This was attributed to the interband e-p scattering in transition m etals.

However, we believe there are strong objections to this modi ed BG model: (i) a cubic (T) dependence is a theoretical model for large angle e-p scattering and no evidence of it was observed in transition and non-transition m etals; (ii) the num erous studies of the (T) dependence in transition m etals have been found to be consistent with a sum of electron-electron e-e, T<sup>2</sup>, and e-p, T<sup>5</sup>, contributions to the low T resistivity, which may easily be confused with a T<sup>3</sup> law [11, 19, 20]; (iii) the interband e-p scattering plays no role in norm al transport in the two band m odel for M gB<sub>2</sub> [12].

In order to solve these problem s, we added e-e scatterring  $T^2$  term in Eq. (1) [19, 20] as a possible scenario. Indeed, keeping in m ind that the BG term is proportional to  $T^{5}$  at  $T < 0:1T_{R}$ , (T) dependence m ay be presented in a simple way [19, 20]: [(T)  $(0) = T^2 = + T^3$ . Here and =  $497:6_1 = T_R^5$  are parameters of e-e and ep scattering term s, respectively. Such a plot should yield a straight line with slope of and its intercept with yaxis (T = 0) should equal to . Further, to be consistent with BG law, the parameter should lead to the same  $T_D$  as obtained from high T log-log t in Fig. 3, and both coe cients must be independent of (0). We determ ined (0) from the intercept of linear (T) vs  $T^2$  dependence with the T = 0 axis and plotted the [(T))  $(0) \models T^2$  vs.  $T^{3}$  in Fig. 4. It is evident that the measured resistivity approaches a quadratic law at T < 25 K in  $ZrB_{12}$ , at T < 100 K in  $ZrB_2$ , and at T < 150 K in both MgB<sub>2</sub> sam ples.

The regime of applicability of two term t is limited to temperatures below  $0.1T_R$ . At larger T the e-p term increases more slowly than T<sup>5</sup> law and this is why the data are not consistent any more with the two terms equation. From the intercept with T = 0 axis, we nd very similar values of for ZrB<sub>12</sub> and ZrB<sub>2</sub> samples in the basalplane ( = 22 p cm K <sup>2</sup> and 15 p cm K <sup>2</sup>, respectively) while is about vetimes larger for C aM gB<sub>2</sub> sample, 95 p cm K <sup>2</sup>. The slopes of give <sub>1</sub> and T<sub>R</sub> values largely consistent with high temperature log-log ts for the ZrB<sub>12</sub> and ZrB<sub>2</sub> samples.

How ever, low T results for and  $_1$  are far from consistent with high T data for both M gB<sub>2</sub> and C aM gB<sub>2</sub> samples. Nevertheless, the magnitude of T<sub>R</sub> = 900 K for M gB<sub>2</sub> extracted from log-log t above 150 K, is in excellent agreement with T<sub>D</sub> = 920 K obtained from low-temperature speci c heat m easurements [21], and is

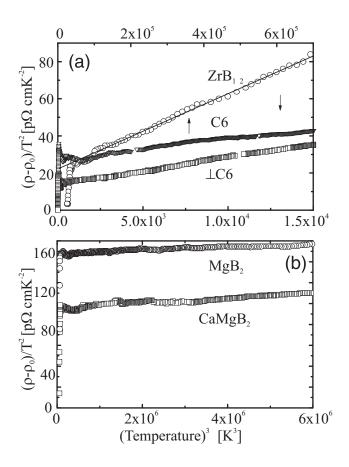


FIG.4: Low tem perature behavior of [(T) (0)  $\models$ T<sup>2</sup> versus T<sup>3</sup> for: (a) ZrB<sub>12</sub> (circles), ZrB<sub>2</sub> in basal plane (squares), ZrB<sub>2</sub> along c (triangles) and (b) MgB<sub>2</sub> (circles) and CaMgB<sub>2</sub> (squares) sam ples.

considerably lower then the reported data based on T<sup>3</sup> dependence of (T) ( $T_R = 1050 \quad 1226 \text{ K}$ , where T<sup>2</sup> term was ignored. [6, 17, 18]). A similar t for theoretical curve is even m ore consistent with  $T_R = 900 \text{ K}$ , how ever we have to mention that violation of M atthiessen's rule in M gB<sub>2</sub> m ay mask the intrinsic (T) dependence [12].

In general, there are m any scattering processes responsible for the T<sup>2</sup> term in (T) of m etals: (i) size, surface, dislocation and in purity scattering induced deviations from M atthiessen's rule (see references in [22]); (ii) e-p scattering for small cylindrical FS sheets relative to the phonon wave vector [16]; (iii) inelastic electron in - purity scattering (e-i) [23]; (iv) the quantum interference between e-i and e-p scattering [24]; (v) e-e scattering [19, 20].

We can estimate some of these elects. We use D rude law to obtain the residual electron mean free path  $1 = 4 v_F = \frac{1}{p}^2$ . Using a Fermi velocity of v = 32 10 cm =s and a plasm a frequency  $\frac{1}{p} = 5.16$  10<sup>5</sup> s<sup>-1</sup> for M gB<sub>2</sub> -band [12], we obtain 1 100 nm. This implies that size elects are negligible for both M gB<sub>2</sub> samples and Zr 4

borides. In agreem ent with  $2rB_2$  data (see Fig. 4) the is proportional to (0) for inelastic e-i scattering [23, 24]. However, this term is 1.5 times low erfor C aM gB<sub>2</sub> relative to M gB<sub>2</sub>, which has the same (0).

We can try to estimate contribution from the small FS sheets to . The T $^2$  term was observed in (T) and electron scattering rates of Bi and Sb, which was attributed to a missing of one q component for e-p scattering on small cylindrical FS sheets [16]. The FS of  ${\rm M}\;{\rm gB}_2$  is composed of two warped open cylinders running along the caxis, which arise from boron orbitals [12, 25]. The FS of ZrB<sub>2</sub> consist of nearly ellipsoidal surfaces joined together at the corners [26, 27], which may also be responsible for the T $^2$  term in (T). We can use the sound velocity s = 1:1 10 cm = s and 8 10 cm = s for  $M gB_2$  and  $ZrB_2$ , respectively [28, 29], to estimate the lowest temperature,  $T_{\text{m in}}$  =  ${\sim}k_{\text{F}}\;\text{s=}k_{\text{B}}$  , when the phonon wave vector q m atches a neck of sm aller tube in M qB<sub>2</sub> (k = 0:129 A <sup>1</sup> [25]) or a diam eter of the ellipsolidal sheets in  $ZrB_2$  (k<sub>F</sub> = 0:095 A<sup>-1</sup>) [26]). We obtain  $T_{m in} = 95 \text{ K}$  and 60 K, respectively. Thus we conclude that  $q < k_F$  at T < 100 K in both diborides, which im plies that the contribution of the 2D FS sheets to is negligible.

In general only um klapp e-e scattering contributes to (T), whereas the norm alcollisions are signi cant in compensated m etals and in them al resistivity [20]. Borides have rather high  $T_D$  which depresses the e-p scattering, so that the e-e SR term is easier to observe. Notice how ever that the value for M gB<sub>2</sub> is ve times larger than corresponding values in ZrB<sub>12</sub> and ZrB<sub>2</sub>. The latter values are in turn ve times larger than in transition m etals ( $_{M o} = 2.5 \text{ p}$  cm =K<sup>2</sup> and  $_{W} = 1.5$  4 p cm =K<sup>2</sup> [19, 20]). Therefore, additional experiments m ust be performed for more pure samples before nal conclusion about the origin of the T<sup>2</sup> term in borides can be drawn.

In conclusion, we present a study of the (T) of single crystals of  $ZrB_{12}$ ,  $ZrB_2$  and polycrystalline samples of M gB<sub>2</sub>. Large di erences between resistive and speci c heat D ebye tem peratures have been observed for  $ZrB_{12}$ . The results provide evidence of a T<sup>2</sup> term for all these borides at low T, whose origin is not yet understood.

## A cknow ledgm ents

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